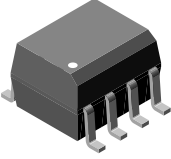
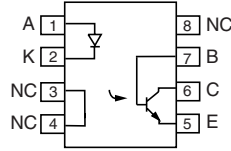


## Optocoupler, Phototransistor Output, with Base Connection in SOIC-8 package



1179002



### DESCRIPTION

The IL211AT/IL212AT/IL213AT are optically coupled pairs with a gallium arsenide infrared LED and silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. The IL211AT/IL212AT/IL213AT comes in a standard SOIC-8 small outline package for surface mounting which makes it ideally suited for high density applications with limited space. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

A choice of 20, 50, and 100 % minimum CTR at  $I_F = 10$  mA makes these optocouplers suitable for a variety of different applications.

### FEATURES

- Isolation test voltage, 4000  $V_{RMS}$
- Industry standard SOIC-8 surface mountable package
- Compatible with dual wave, vapor phase and IR reflow soldering
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### AGENCY APPROVALS

- UL1577, file no. E52744 system code Y
- CUL - file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-5 available with option 1

ORDER INFORMATION	
PART	REMARKS
IL211AT	CTR > 20 %, SOIC-8
IL212AT	CTR > 50 %, SOIC-8
IL213AT	CTR > 100 %, SOIC-8

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Peak reverse voltage		$V_R$	6.0	V
Forward continuous current		$I_F$	60	mA
Power dissipation		$P_{diss}$	90	mW
Derate linearly from 25 °C			1.2	mW/°C
<b>OUTPUT</b>				
Collector emitter breakdown voltage		$BV_{CEO}$	30	V
Emitter collector breakdown voltage		$BV_{ECO}$	7.0	V
Collector base breakdown voltage		$V_{CBO}$	70	V
$I_{CMAX DC}$		$I_{CMAX DC}$	50	mA
$I_{CMAX}$	$t < 1.0$ ms	$I_{CMAX}$	100	mA
Power dissipation		$P_{diss}$	150	mW
Derate linearly from 25 °C			2.0	mW/°C

# IL211AT/IL212AT/IL213AT



Vishay Semiconductors Optocoupler, Phototransistor Output,  
with Base Connection in SOIC-8 package

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>COUPLER</b>				
Isolation test voltage		$V_{ISO}$	4000	$V_{RMS}$
Total package dissipation	LED and detector	$P_{tot}$	240	mW
Derate linearly from 25 °C			3.2	mW/°C
Storage temperature		$T_{stg}$	- 55 to + 150	°C
Operating temperature		$T_{amb}$	- 55 to + 100	°C
Soldering time	at 260 °C		10	s

## Note

$T_{amb} = 25\text{ °C}$ , unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	$I_F = 10\text{ mA}$		$V_F$		1.3	1.5	V
Reverse current	$V_R = 6\text{ V}$		$I_R$		0.1	100	$\mu\text{A}$
Capacitance	$V_R = 0\text{ V}$		$C_O$		13		pF
<b>OUTPUT</b>							
Collector emitter breakdown voltage	$I_C = 10\text{ }\mu\text{A}$		$BV_{CEO}$	30			V
Emitter collector breakdown voltage	$I_E = 10\text{ }\mu\text{A}$		$BV_{ECO}$	7.0			V
Collector dark current	$V_{CE} = 10\text{ V}$		$I_{CEO}$		5.0	50	nA
Collector emitter capacitance	$V_{CE} = 0\text{ V}$		$C_{CE}$		10		pF
<b>COUPLER</b>							
Saturation voltage, collector emitter	$I_F = 10\text{ mA}$		$V_{CEsat}$			0.4	V
Isolation test voltage	1 s		$V_{ISO}$	4000			$V_{RMS}$
Capacitance (input to output)			$C_{IO}$		0.5	50	pF
Resistance (input to output)			$R_{IO}$		100		$G\Omega$
Collector emitter breakdown voltage	$I_C = 10\text{ }\mu\text{A}$		$BV_{CEO}$	30			V

## Note

$T_{amb} = 25\text{ °C}$ , unless otherwise specified.

Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$	IL211AT	CTR	20	50		%
		IL212AT	CTR	50	80		%
		IL213AT	CTR	100	130		%

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Switching time	$I_C = 2\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $V_{CC} = 10\text{ V}$		$t_{on}$ , $t_{off}$		3.0		$\mu\text{s}$



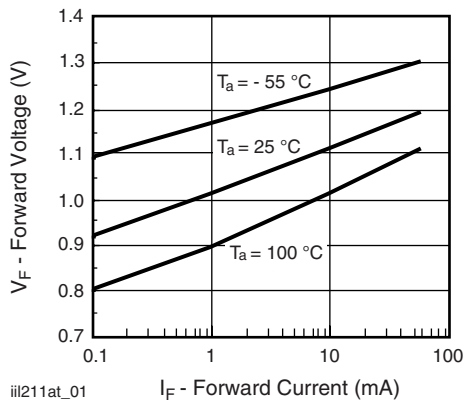
SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
$V_{IOTM}$			6000			V
$V_{IORM}$			560			V
$P_{SO}$					350	mW
$I_{SI}$					150	mA
$T_{SI}$					165	°C
Creepage distance			4			mm
Clearance distance			4			mm
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.2			mm

**Note**

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

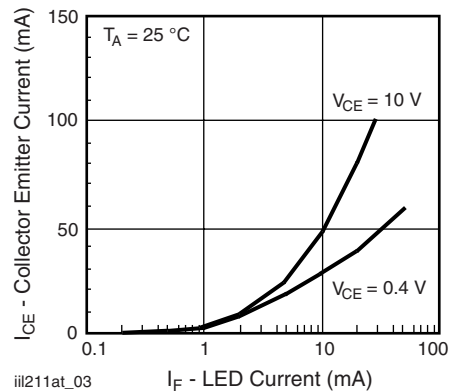
**TYPICAL CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$ , unless otherwise specified



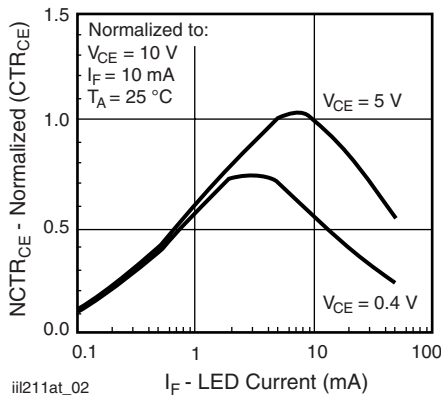
iii211at\_01

Fig. 1 - Forward Voltage vs. Forward Current



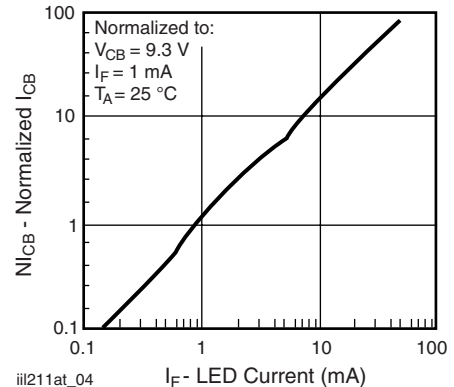
iii211at\_03

Fig. 3 - Collector Emitter Current vs. LED Current



iii211at\_02

Fig. 2 - Normalized Non-Saturated and Saturated  $CTR_{CE}$  vs. LED Current



iii211at\_04

Fig. 4 - Normalized Collector Base Photocurrent vs. LED Current

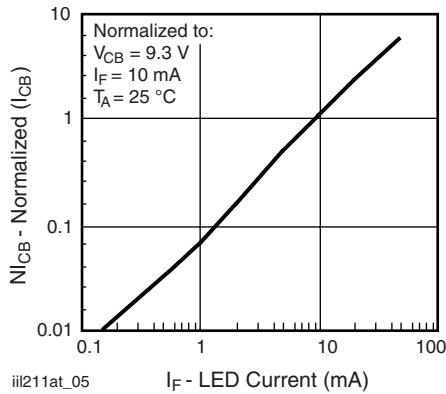


Fig. 5 - Normalized Collector Base Photocurrent vs. LED Current

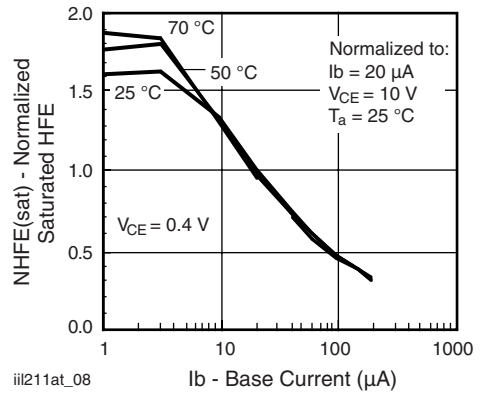


Fig. 8 - Normalized Saturated  $h_{FE}$  vs. Base Current and Temperature

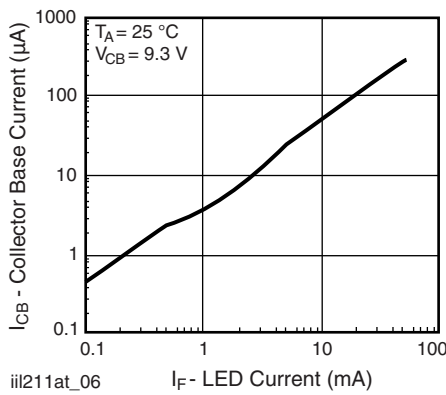


Fig. 6 - Collector Base Photocurrent vs. LED Current

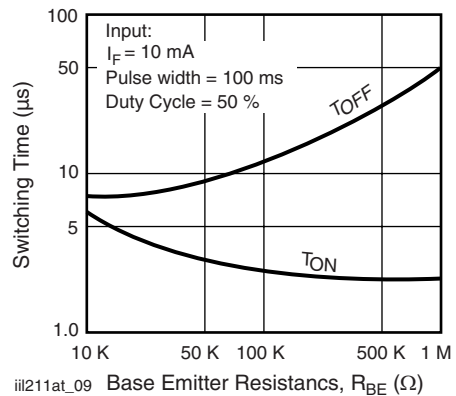


Fig. 9 - Typical Switching Characteristics vs. Base Resistance (Saturated Operation)

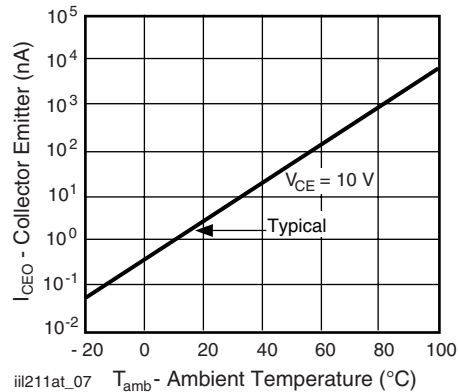


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

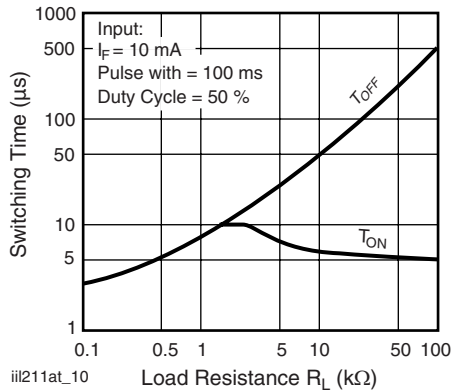
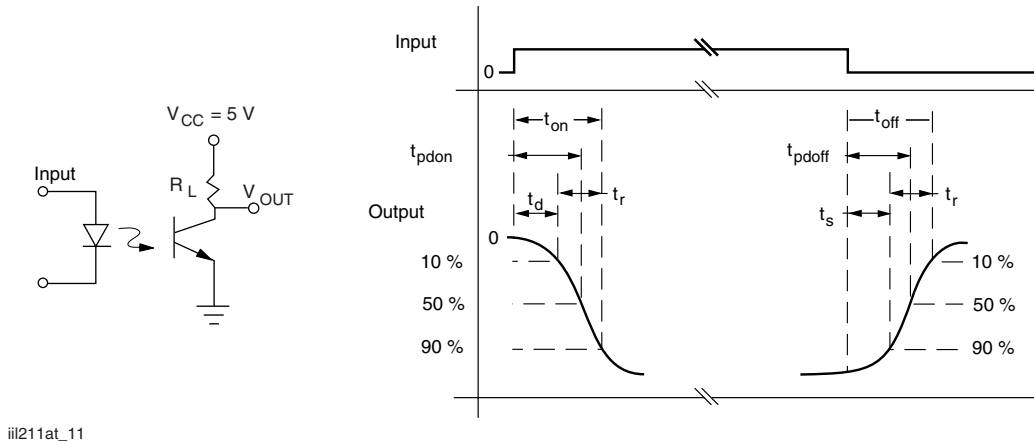


Fig. 10 - Typical Switching Times vs. Load Resistance



# IL211AT/IL212AT/IL213AT

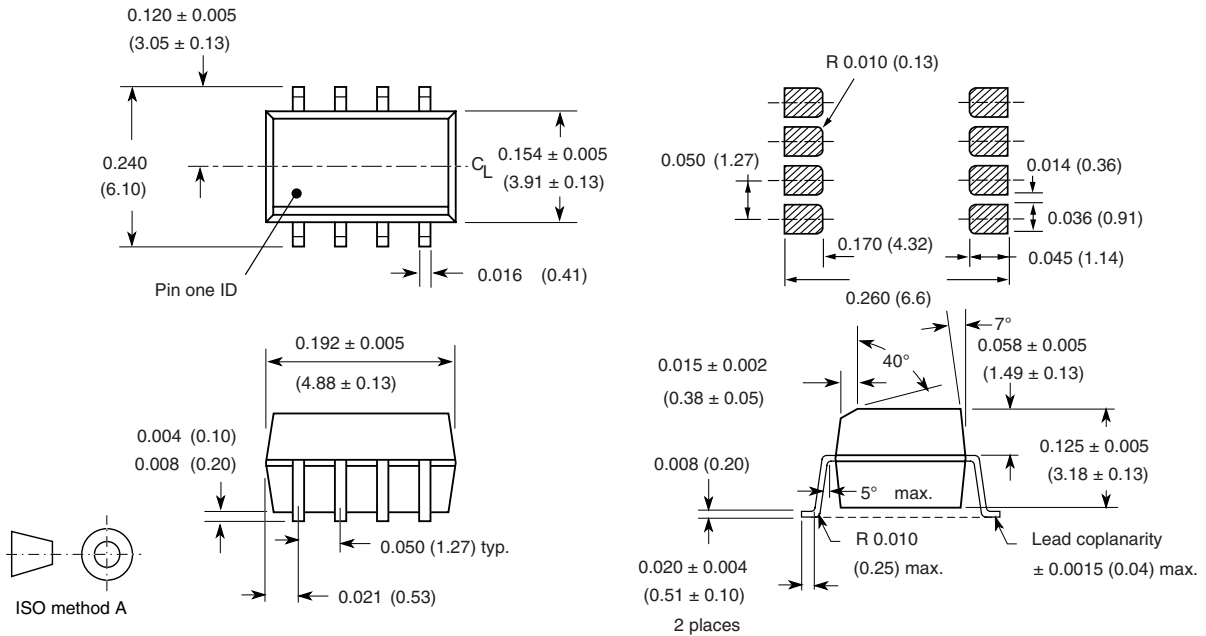
Optocoupler, Phototransistor Output, Vishay Semiconductors  
with Base Connection in SOIC-8 package



iii211at\_11

Fig. 11 Switching Test Circuit

## PACKAGE DIMENSIONS in inches (millimeters)



i178003

## **OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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